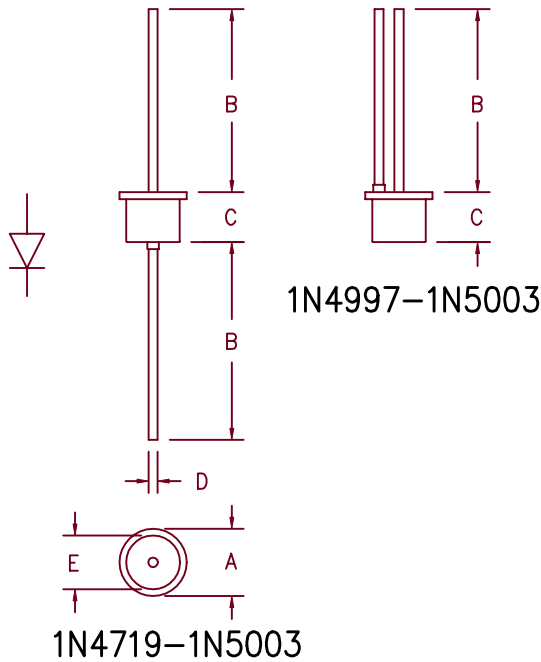


Silicon Rectifiers

1N4719–1N4725, 1N4997–1N5003



| Dim. | Inches | | Millimeter | | Notes |
|------|---------|---------|------------|---------|-------|
| | Minimum | Maximum | Minimum | Maximum | |
| A | --- | .450 | --- | 11.43 | Dia. |
| B | .980 | --- | 24.89 | --- | |
| C | --- | .300 | --- | 7.62 | |
| D | .046 | .056 | 1.17 | 1.42 | Dia. |
| E | --- | .350 | --- | 8.89 | Dia. |

| Microsemi Catalog Number | Peak Reverse Voltage |
|--------------------------|----------------------|
| 1N4719, 1N4997 | 50V |
| 1N4720, 1N4998 | 100V |
| 1N4721, 1N4999 | 200V |
| 1N4722, 1N5000 | 400V |
| 1N4723, 1N5001 | 600V |
| 1N4724, 1N5002 | 800V |
| 1N4725, 1N5003 | 1000V |

- High Surge Capability
- 175°C Junction Temperature
- VRRM 50 to 1000 Volts
- 3 Amp Current Rating
- Hermetically Sealed

| Electrical Characteristics | | |
|--|----------------------|--|
| Average forward current | IF(AV) 3.0 Amps | $T_A = 119^\circ\text{C}$, Square wave, $R_{\theta J L} = 12^\circ\text{C/W}$, $L = 1/4"$ 8.3ms, half sine, $T_J = 175^\circ\text{C}$ $I_{FM} = 3.0\text{A}$; $T_J = 25^\circ\text{C}^*$ $V_{RRM, T_J} = 25^\circ\text{C}$ |
| Maximum surge current | IFSM 300 Amps | |
| Max peak forward voltage | VFM 1.0 Volts | |
| Max peak reverse current | IRM 25 μA | |
| *Pulse test: Pulse width 300 μsec , Duty cycle 2% | | |

| Thermal and Mechanical Characteristics | | |
|--|-----------------------------|--------------------------------|
| Storage temperature range | T_{STG} | -65°C to 175°C |
| Operating junction temp range | T_J | -65°C to 175°C |
| Maximum thermal resistance | $L = 1/4"$ $R_{\theta J L}$ | 12°C/W Junction to Lead |
| Weight | | .08 ounces (2.3 grams) typical |

11-13-00 Rev. 1

1N4719–1N4725, 1N4997–1N5003

Figure 1
Typical Forward Characteristics

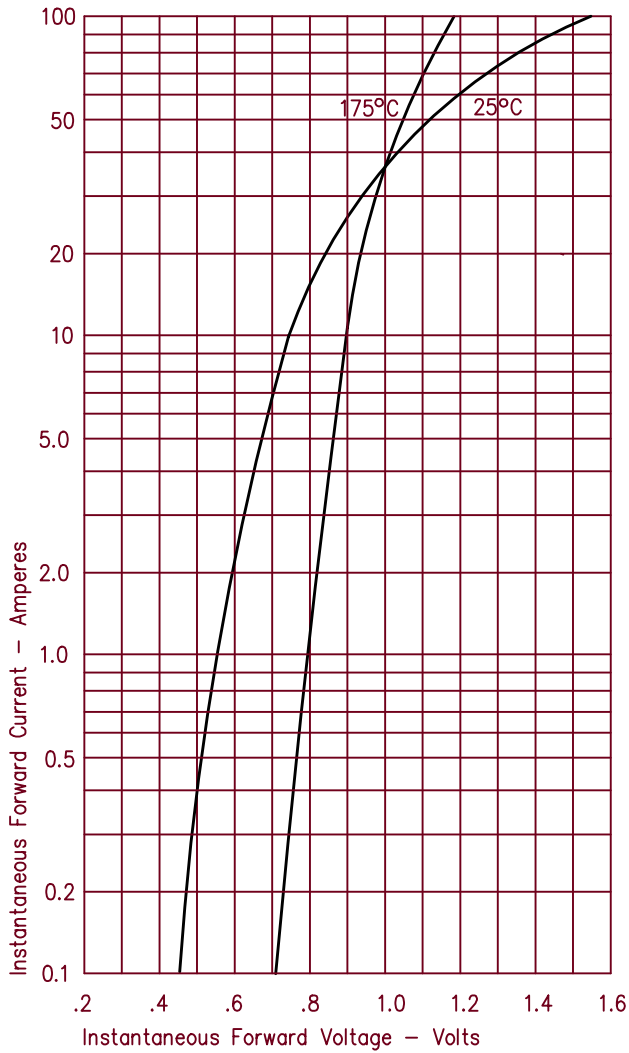


Figure 3
Forward Current Derating

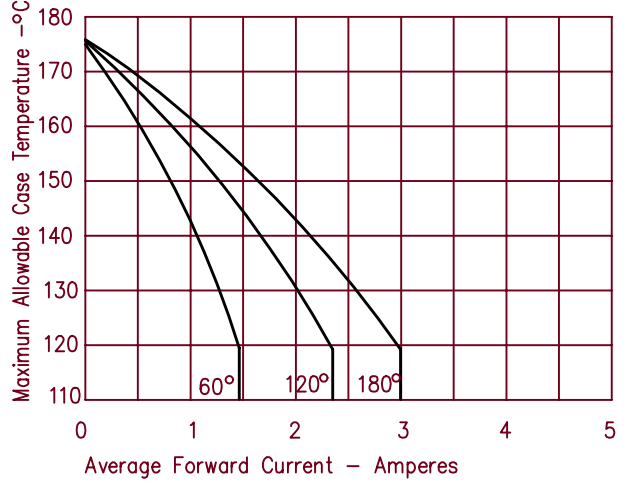


Figure 2
Typical Reverse Characteristics

